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THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of:

Robert J. SMALL et al.

Confirmation No.:

Serial No.:

10/665,417

Art Unit:

1755

Filed:

September 22, 2003

Examiner:

Marcheschi, Michael

For:

METHOD OF CHEMICAL

Attorney Docket No.: 060937-0215-US

MECHANICAL PLANARIZATION

(Formerly P&E)

(8317-0215-999)

SUBMISSION OF REVOCATION OF ORIGINAL POWER OF ATTORNEY AND GRANT OF NEW POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Enclosed is a copy of the Revocation of Original Power of Attorney and Grant of New Power of Attorney by the Assignee, EKC Technology, Inc. Assignee directs the Patent and Trademark Office to send all future correspondence to:

> **CUSTOMER NO. 009629** MORGAN, LEWIS & BOCKIUS LLP

1111 Pennsylvania Avenue, N.W. Washington, D.C. 20004 Tel. 202-739-3000

If there is any fee due in connection with the filing of this Submission, please charge the fee to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

Date:

April 20, 2004

Respectfully submitted

Christopher G. Hayden

(Reg. No.)

Morgan, Lewis & Bockius LLP 1111 Pennsylvania Avenue, N.W.

Washington, D.C. 20004

(202) 739-3001



REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Assignee:

EKC Technology, Inc.

Date: 29 March 2004

Signature:

Typed Name 'Michael A.

Position/Title Vice President, R&D and Engineering

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Hayward, California 94545



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App.#	State Stille	s Inventor(s)	Filing &	New Atloriey Docket No	Former Attorney
	Compositions for Cleaning Organic			The state of the s	
	and Plasma Etched Residues for				,
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
	Method of and Apparatus for				
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
	Chemical Mechanical Polishing				
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
•	Oxalic Acid as a Semiaqueous				
10/424 706	Cleaning Product for Copper and Dielectrics	Locatel	04/24/2002	60007 446 116	0047 440 000
10/421,706	Sulfoxide Pyrolid(in)one Alkanolamine	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
10/100,100	Cicarior Composition	Zilou, ct at.	01712/2002	00937-110-03	0317-110-999
	Method for the Deposition of Materials				·
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
	Post Etch Cleaning Composition for				
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
	Photolytic Conversion Process to				
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation			·	
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
40/000 400	Chemically Treating A Substrate		0.1/00/0000		
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including	•		1	
	Nucleophilic Amine Compound Having Reduction and Oxidation				
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-133-US	8317-137-999
10/440,127	Process for the Use of Bis-Choline	Wiciviii IV. Oalter	00/30/2003	00937-137-03	0317-137-999
	and Tris-Choline in the Cleaning of				
	Quartz-Coated Polysilicon and Other	*			
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
.0,000,001	Cleaning Compositions Containing	Onaim, ot al.	10,22,200	00001-109-00	0017-103-333
	Hydroxylamine Derivatives and	! : :			•
, ·	Process Using Same for Residue	l İ		· · ·	•
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
	Composition for Exfoliation Agent to	İ		_	
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Reducing Oxide Loss When Using				
	Fluoride Chemistries to Remove Post-			,	
	Etch Residues in Semiconductor				Ì
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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Appalla	True 5 7	nventor(s) / / it	Date 2	Docket No.	ADőčket No.
10/630,301	Method for Depositing Patterned Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
10/030,001	Methods for the Deposition of Silver	11111, 01 01.	01700/2000	00007 140 00	0011-140-999
	and Silver Oxide Films and Patterned			Ì	·
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	Semiconductor Process Residue				
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	System and Method for Cleaning				
	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
				·	
	Abrasive-Free Chemical Mechanical	,			
	Polishing Composition and Polishing				
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Potol of al	10/21/2003	60937-152-US	9247 452 000
10/009,042	Wet Etch of Thanlant-Tungsten Fillit	Patel, et al.	10/21/2003	00937-132-03	8317-152-999
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
10/201,101	Hydrothermal Treatment of	•			
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
	Chemical Mechanical Polishing				
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Aqueous Phosphoric Acid				
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
	Load Lock System for Supercritical	_			
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/405 005	Automated Dense Phase Fluid	Frincial at all	00/49/0000	60007 476 116	9247 470 000
10/465,905	Cleaning System Residue Removers for	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Electrohydrodynamic Cleaning of				•
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
00/400,400	Free Radical-Forming Activator	1 toboit of official		00007 170111	0017 170 000
	Attached to Solid and Used to		•	·	
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
10/001,022	Titanium Carboxylate Films for Use in	goon, or an	02/11/2000	00007 175 00	
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing			·	,
]	Fluoride for Use During	·			
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
	Cleaning Composition for Removing	•			
	Resists and Manufacturing Method of		• ,		
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
10440	Deposition of Permanent Polymer	_			
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	.8317-187-999

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	Seimconductor Process Residue				
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of		07/00/0000	00007.404.410	0047.404.000
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				•
60/549 227	Rapidly Removing Overfilled Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
60/518,337	CMP Method for Copper, Tungsten,	Oriene, et al.	11/10/2003	00337-200-110	0017-200-000
	Titanium, Polysilicon, and Other	·	,		
	Substrates Using Organosulfonic				
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
10,000,020	PeriodicAcid Compositions for				
	Polishing Nobel Metal/High K	· .			
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
	Cerium Oxide Abrasives for Chemical				
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
<u> </u>	Ot 1 111 to the Delianian	•			
	Chemical Mechanical Polishing				
00/540 720	Slurries and Cleaners Containing Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
60/516,736	Periodic Acid Compositions for	Carter, et al.	17/04/2003	00937-200-110	0317-200-000
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
00/404,000	Chemical Mechanical Polishing	11000110.01110.1			
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical	 			
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
ļ	Chemical Mechanical Polishing				
•	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				·
10/005 117	Mechanical Planarization of Tantalum and Tantalum Nitride	Small at al	09/22/2003	60937-215-US	8317-215-999
10/665,417	Alumina Abrasive for Chemical	Small, et al.	09/22/2003	60937-213-03	0317-213-999
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
00/320,107	Particulate or Particle-Bound	Oriono, ot al.	12.02.2000		
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound				
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water	·			
60/533,054	Polishing with Ceria Slurries	Yu, et al	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and		1		i İ
	Copper Contamination From Low-K	,	1		
60/544 040	Dielectrics Using Superciritcal CO2 with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
60/511,949	Method and Apparatus for Substrate	Jeronie Daviot	10/14/2003	00931-223-FR	0517-225-000
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999
10,007,009	1.10 1100				

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	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888